ASSIGNMENT-2

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1)Mosfet Resistance

Taking W/L=240/180 and simulating the Mosfet,

a) For NMOS, considering Vdd=1.8V and initial voltage across capacitor as 1.8V.

Netlist file:

```
*Title:Q1a- NMOS Resistance
.include TSMC180.lib
.model nch_tt nmos
*Netlist
M1 ds gs 0 0 nch_tt W=0.24u L=0.18u
Vdd gs 0 DC 1.8
C1 c1 0 1pF
V2 c1 ds DC 0
.IC V(C1)=1.8
.tran 0.0005u 50u
.control
plot i(V2) vs V(ds)
let Req = V(ds)/i(V2)
meas tran t2 find time when v(c1)=0.9
meas tran ravg AVG Req from=0 to=t2
plot v(c1)
plot Req vs V(ds)
.endc
.end
```

Simulation result:

```
sivani@sivani-Inspiron-5558: ~/A2
File Edit View Search Terminal Help
 Circuit: *title:q1a- nmos resistance
Doing analysis at TEMP = 27.000000 and TNOM = 27.000000
Warning: Pd = 0 is less than W.
Warning: Ps = 0 is less than W.
Initial Transient Solution
Node
                                            Voltage
ds
                                                1.8
v2#branch
vdd#branch
                                       0.000205522
 Reference value: 4.61536e-05
No. of Data Rows : 100008
                         4.504998e-09
                      = 6.879962e+03 from= 0.000000e+00 to= 4.640000e-09
ngspice 1 ->
```

So, We will get Req at Vdd=1.8V as $6.879k\Omega$.

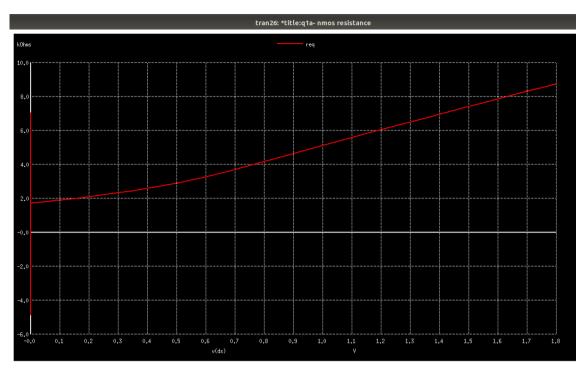


Fig-1:R Vs Vdd Graph(at Vdd=1.8V)

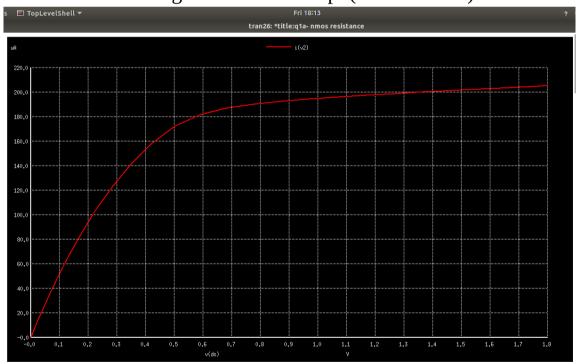


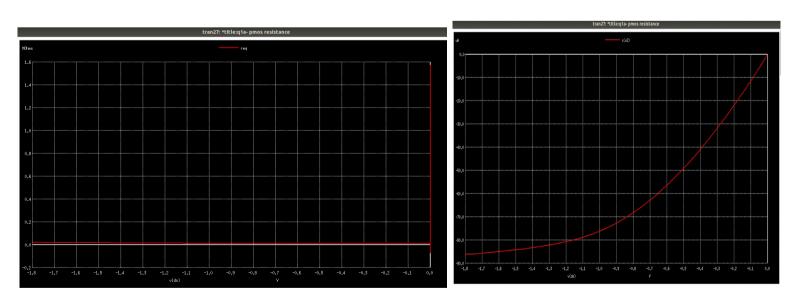
Fig -2: Id Vs Vds graph of NMOS

Similarly for PMOS simulation results are

Netlist file:

```
*Title:Q1a- PMOS Resistance
   include TSMC180.lib
   .model pch_tt pmos
  *Netlist
 M1 ds gs 0 0 pch_tt W=0.24u L=0.18u
Vdd gs 0 DC -1.8
C1 c1 0 1pF
V2 c1 ds DC 0
  .IC V(C1)=-1.8
.tran 0.0005u 50u
.control
 run
plot i(V2) vs V(ds)
let Req = V(ds)/i(V2)
meas tran t2 find time when v(c1)=-0.9
meas tran ravg AVG Req from=0 to=t2
plot v(c1)
plot Req vs V(ds)
  .endc
  .end
                                              sivani@sivani-Inspiron-5558: ~/A2
                                                                                                                            File Edit View Search Terminal Help
unrecognized parameter (xl) - ignored
unrecognized parameter (xw) - ignored
Doing analysis at TEMP = 27.000000 and TNOM = 27.000000
Warning: Pd = 0 is less than W.
Warning: Ps = 0 is less than W.
Initial Transient Solution
                                                                Voltage
ds
gs
c1
v2#branch
vdd#branch
 Reference value : 4.84216e-05
No. of Data Rows : 100008
                                = 1.104266e-08
= 1.645679e+04 from= 0.000000e+00 to= 1.114000e-08
```

So, We will get Req at Vdd=1.8V as $16.45k\Omega$.



R Vs Vdd Graph for pmos(at Vdd=1.8V)

Id Vs Vdd Graph for pmos

b) Req for different Vdds in nmos and pmos

For NMOS: Netlist file:

```
*Title:Q1b- NMOS Resistance with varying Vdd

.include TSMC180.lib
.model nch_tt nmos

*Netlist

M1 ds gs 0 0 nch_tt W=0.24u L=0.18u
Vdd gs 0 DC 0.6
C1 c1 0 1pF
V2 c1 ds DC 0

.IC V(C1)=0.6
.tran 0.0005u 50u
.control

run
plot i(V2) vs V(ds)
let Req = V(ds)/i(V2)
meas tran t2 find time when v(c1)=0.3
meas tran ravg AVG Req from=0 to=t2
plot v(c1)
plot Req vs V(ds)
.endc
.end
```

For Vdd=1.8V:

```
sivani@sivani-Inspiron-5558: ~/A2

File Edit View Search Terminal Help

Circuit: *title:q1a- nmos resistance

Doing analysis at TEMP = 27.000000 and TNOM = 27.000000

Warning: Pd = 0 is less than W.

Warning: Ps = 0 is less than W.

Initial Transient Solution

Node Voltage

...

ds 1.8

gs 1.8

c1 1.8

v2#branch 0.000205522

vdd#branch 0.000205522

vdd#branch 0

Reference value: 4.61536e-05

No. of Data Rows: 100008

t2 = 4.504998e-09

rayg = 6.879962e+03 from= 0.0000000e+00 to= 4.640000e-09

ngspice 1 -> □
```

So,When Vdd=1.8V ,Req=6.879k Ω .

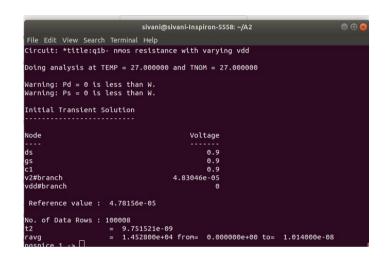
For Vdd=1.5V:

So,When Vdd=1.5V ,Req=7.7k Ω .

For Vdd=1.2V:

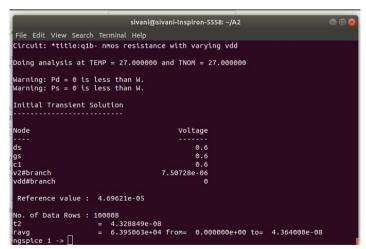
So,When Vdd=1.2V ,Req=9.325k Ω .

For Vdd=0.9V:



So,When Vdd=0.9V ,Req=14.528k Ω .

For Vdd=0.6V:



So,When Vdd=0.6V ,Req=63.95k Ω .

Similarly,
For PMOS
Netlist file:

```
*Title:Q1b- PMOS Resistance with varying Vdd

.include TSMC180.lib
.model pch_tt pmos

*Netlist

M1 ds gs 0 0 pch_tt W=0.24u L=0.18u
Vdd gs 0 Dc -0.6
C1 c1 0 1pF
V2 c1 ds DC 0

.IC V(C1)=-0.6
.tran 0.0005u 50u
.control

run
plot i(V2) vs V(ds)
let Req = V(ds)/i(V2)
meas tran t2 find time when v(c1)=-0.3
meas tran ravy AVG Req from=0 to=t2
plot v(c1)
plot Req vs V(ds)
.endc
.end
```

For Vdd=1.8V:

So,When Vdd=1.8V Req=16.45k Ω .

For Vdd=1.5V:

So,When Vdd=1.5V Req=21.656k Ω .

For Vdd=1.2V:

```
sivani@sivani-Inspiron-5558: ~/A2

File Edit View Search Terminal Help
unrecognized parameter (xl) - ignored
unrecognized parameter (xw) - ignored
Doing analysis at TEMP = 27.0000000 and TNOM = 27.000000

Warning: Pd = 0 is less than W.
Warning: Ps = 0 is less than W.

Initial Transient Solution

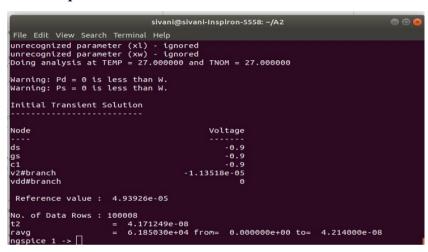
Node Voltage
---
ds -1.2
gs -1.2
c1 -1.2
v2#branch -2.90118e-05
vdd#branch 0

Reference value : 4.85591e-05

No. of Data Rows : 100008
t2 = 2.182223e-08
ravg = 3.237323e+04 from= 0.0000000e+00 to= 2.214000e-08
nossice 1 -> □
```

So,When Vdd=1.2V Req=32.37k Ω .

For Vdd=0.9V:



So,When Vdd=0.9V Req=61.85k Ω .

For Vdd=0.6V:

So,When Vdd=0.6V Req=250.3k Ω . Writing these results in a table gives,

	Vdd=1.8V	Vdd=1.5V	Vdd=1.2V	Vdd=0.9V	Vdd=0.6V
NMOS(in $k\Omega$)	6.879	7.7	9.325	14.528	63.95
PMOS(in $k\Omega$)	16.45	21.656	32.37	61.85	250.3

2) Mosfet Capacitance

a) Given W/L=2.5

For Short channel NMOS(L=0.18um,W=0.45um)

Simulation results are

.endc

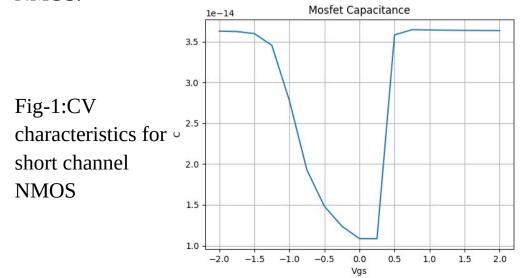
```
Netlist file: *Title:Q2a-Short channel NMOS CV
                        .include "TSMC180.lib"
.model nch_tt nmos
                        Ygs1 n1 0 DC 2

Ygs2 T n1 DC 0 AC 1 SINE(0 0.003183 50)

M1 0 G 0 0 nch_tt W=0.45u L=10u

Vt T G DC 0
                      xlabel "Current waveform at VCM $&vgs1"
```

Through this simulation, we will get values of C and Vgs. Then plot these points in python results in Mosfet Capacitance graph for short channel NMOS.



```
import numpy as np
import matplottib.pyplot as plt

pl=[3.638e-14,1.75]
p3=[3.638e-14,1.5]
p4=[3.641e-14,1.25]
p5=[3.644e-14,1.25]
p5=[3.644e-14,0.75]
p7=[3.584e-14,0.75]
p8=[1.085e-14,0.25]
p8=[1.085e-14,0.25]
p1=[1.288e-14,0.25]
p1=[1.288e-14,0.75]
p1=[1.292e-14,-0.75]
p13=[2.779e-14,-1]
p14=[3.456e-14,-1.25]
p15=[3.6e-14,-1.25]
p15=[3.6e-14,-1.25]
p15=[3.6e-14,-1.5]
p16=[3.625e-14,-1.75]
p17=[3.63e-14,-2]

x_val=[p1[0],p2[0],p3[0],p4[0],p5[0],p6[0],p7[0],p8[0],p9[0],p10[0],p11[0],p12[0],p13[0],p14[0],p15[0],p16[1],p11[1])
plt.plot(y_val_x_val_)
plt.ylade("Vys")
plt.xlabel("Vys")
plt.xlabel("Vos")
plt.show()
```

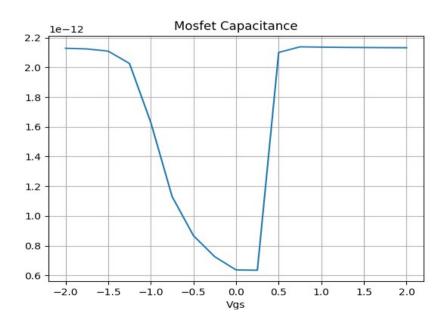
For Long channel NMOS(L=25um,W=10um)

Simulation results are

Netlist file:

Through this simulation,we will get values of C and Vgs.Then plot these points in python results in Mosfet Capacitance graph for long channel NMOS.

Fig-2:CV characteristics for long channel NMOS



```
import numpy as np
import matplotlib.pyplot as plt

pl=[2.13297e-12,2]
p2=[2.133627e-12,1.75]
p3=[2.134473e-12,1.5]
p4=[2.1356e-12,1.25]
p5=[2.137e-12,1]
p6=[2.139e-12,0.75]
p7=[2.101e-12,0.5]
p8=[6.35e-13,0.25]
p9=[6.37e-13,0]
p10=[7.26e-13,-0.25]
p11=[8.68e-13,-0.5]
p11=[8.68e-13,-0.5]
p12=[1.131e-12,-0.75]
p13=[1.63e-12,-1]
p14=[2.027e-12,-1.25]
p15=[2.11e-12,-1.5]
p16=[2.125e-12,-1.75]
p17=[2.129e-12,-2]
x val=[p1[0],p2[0],p3[0],p4[0],p5[0],p6[0],p7[0],p8[0],p9[0],p10[0],p11[0],p12[0],p13[0],p14[0],p15[0],p16[0],p17[0]]
y val=[p1[1],p2[1],p3[1],p4[1],p5[1],p6[1],p7[1],p8[1],p9[1],p10[1],p11[1],p12[1],p13[1],p14[1],p15[1],p15[1],p17[1]]
plt.ylabel(""")
plt.xlabel(""")
plt.xlabel(""s)
plt.title("Mosfet Capacitance")
plt.show()
```

b)CV characteristics with change of frequency

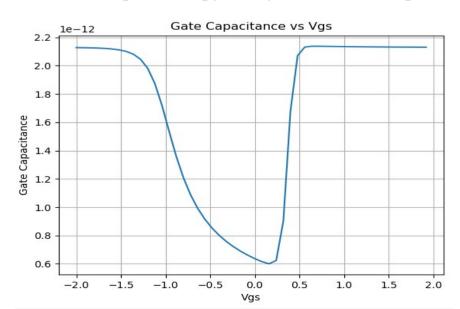
For long channel nmos,

with f=10M Hz

Netlist file:

Plotting these simulation points in python yields mosfet capacitance graph

as



With f = 10GHz,

Netlist file:

```
*Title:Q2b-Long channel NMOS CV

.include "TSMC180.lib"
.model nch_tt nmos

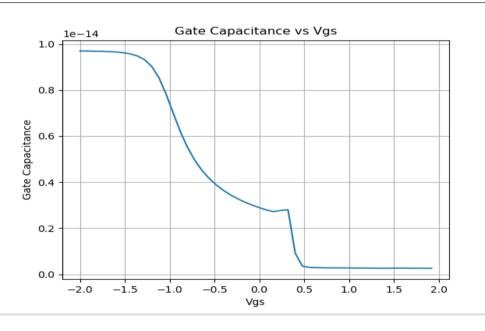
*Netlist
Vgs1 n1 0 DC 2
Vgs2 T n1 DC 0 AC 1 SINE(0 0.159e-10 10e9)
M1 0 G 0 0 nch_tt W=25u L=10u
Vt T G DC 0

.control
run
let vgs1 = 2
while vgs1 >= -2
alter @Vgs1 vgs1
tran 10u 20m
meas tran c1 FIND i(Vt) AT = 20m
print vgs1
plot i(Vt) xlabel "Current waveform at VCM $&vgs1"
let vgs1 = vgs1 - 0.25

end
.endc
.endc
.endc
```

Plotting these simulation points in python yields mosfet capacitance graph

as



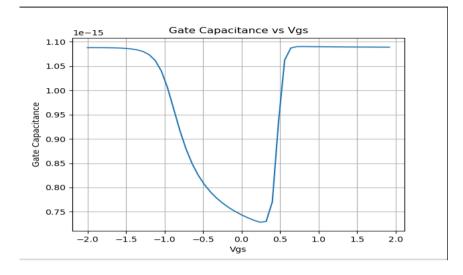
For short channel NMOS,

with f=10M Hz,

Netlist file:

Plotting these simulation points in python yields mosfet capacitance graph

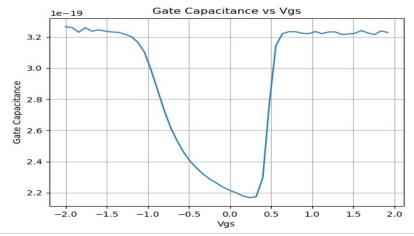
as



With f = 10GHz,

Netlist file:

Plotting these simulation points in python yields mosfet capacitance graph as



5)NMOS Inverter

Results obtained analytically in question-4 are:

 V_{OH} =2.5V V_{iL} =0.3837 V Noise margin low=0.3597 V

 V_{OL} =24.08mV V_{iH} =0.684 V Noise margin high=1.816 V

 V_{M} =0.6403 V Peak gain=-10.399

Now we shall compare these with simulations

a) Simulating the given circuit

Netlist File:

```
*Title:Q5a-Gain of NMOS Inverter
 .include TSMC180.lib
 .model nch_tt nmos
Vdd 1 0 2.5
VGG 10 2.7
Rl 1 out 75k
Vin in 0 1
M1 out in 0 0 nch_tt W=0.54u L=0.18u
.control
dc Vin 0 3 0.01
dc Vin 0 3 0.01
let gain = deriv(V(out))
plot gain
meas dc Vol find V(out) at=2.5 cross=1
meas dc Voh find V(out) at=0
meas dc Vm find V(out) when V(out)=V(in)
meas dc Vil when gain=-1 cross=1
meas dc Vih when gain=-1 cross=2
let NMh = Voh-Vih
let NMl = Vil-Vol
print NMh
print NMh
print NMl
meas dc peakgain MIN gain
plot V(out)
 .endc
  end
                                                       sivani@sivani-Inspiron-5558: ~/A2
  No. of Data Rows : 2008
                                               -4.381621e-30
 vgs1 = -2.00000e+00
ngspice 1 -> Q5a.net
  Circuit: *title:q5a-gain of nmos inverter
 Doing analysis at TEMP = 27.000000 and TNOM = 27.000000
 Warning: Pd = 0 is less than W.
Warning: Ps = 0 is less than W.
        of Data Rows : 301
                                             3.174192e-02
2.499998e+00
6.731995e-01
3.871599e-01
7.738449e-01
```

-9.515716e+00 at= 6.500000e-01

From these simulations we obtained,

 V_{OH} =2.499V V_{iL} =0.3871 V Noise margin low=0.3554 V

 V_{OL} =31.7mV V_{iH} =0.7738 V Noise margin high=1.726 V

 V_{M} =0.673 V Peak gain= -9.515

So, These simulation results are similar to analytical values.

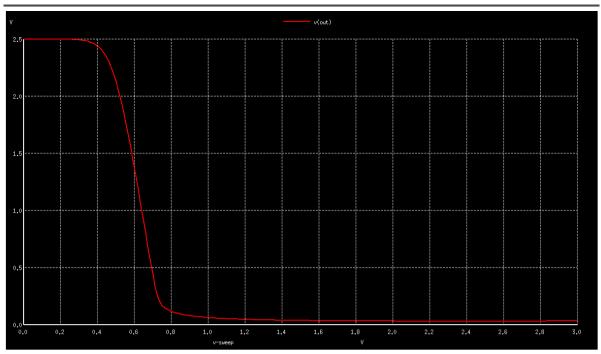


Fig:Graph of Vout

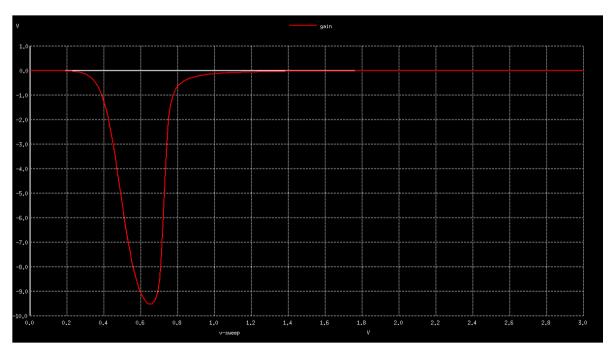


Fig:Plot of Gain of Inverter

b)Impact of load resitance on threshold($V_{\rm M}$) and peak-gain of Inverter.

Let us consider R_L =6 $k\Omega$ and simulate

Netlist file:

```
.include TSMC180.lib
.model nch_tt nmos

*Netlist
Vdd 1 0 2.5
Rl 1 out 6k
Vin in 0 1
M1 out in 0 0 nch_tt W=0.54u L=0.18u
.control
dc Vin 0 3 0.01
let gain = deriv(V(out))
plot gain
meas dc Vol find V(out) at=2.5 cross=1
meas dc Voh find V(out) when V(out)=V(in)
meas dc Vil when gain=-1 cross=1
meas dc Vih when gain=-1 cross=2
let NMh = Voh-Vih
let NMl = Vil-Vol
print NMh
print NMl
meas dc peakgain MIN gain
plot V(out)
.endc
.end
```

```
sivani@sivani-Inspiron-5558: ~/A2

File Edit View Search Terminal Help

Error(parse.c--checkvalid): vil: no such vector.

Error(parse.c--checkvalid): nmh: no such vector.

Error(parse.c--checkvalid): nmh: no such vector.

peakgain = -3.092402e-01 at= 1.2200000e+00

ngspice 1 -> Q5a.net

Circuit: *title:q5b-gain of nmos inverter

Doing analysis at TEMP = 27.000000 and TNOM = 27.000000

Warning: Pd = 0 is less than W.

Warning: Ps = 0 is less than W.

No. of Data Rows : 301

vol = 4.285629e-01

voh = 2.500000e+00

vm = 1.282686e+00

vil = 5.615429e-01

vih = 7.838880e-01

nmh = 7.838880e-01

nmh = 7.838880e-01

nmh = 7.838880e-01

nmh = 1.329800e-01

peakgain = -1.680549e+00 at= 1.150000e+00

ngspice 1 -> □
```

Let us consider R_L =1G Ω and simulate

Netlist file:

```
*Title:Q5b-Gain of NMOS Inverter
      include TSMC180.lib
      .model nch tt nmos
     Vdd 1 0 2.5
Rl 1 out 1e9
     M1 out in 0 0 nch_tt W=0.54u L=0.18u
    .control
dc Vin 0 3 0.01
let gain = deriv(V(out))
plot gain
meas dc Vol find V(out) at=2.5 cross=1
meas dc Voh find V(out) at=0
meas dc Vin when gain=-1 cross=1
meas dc Vih when gain=-1 cross=2
let NMh = Voh-Vih
let NMl = Vil-Vol
print NMh
print NMh
meas dc peakgain MIN gain
plot V(out)
      .endc
                                               sivani@sivani-Inspiron-5558: ~/A2
                                   = 1.716112e+00
nmh = 7.838880e-01
nml = 1.329800e-01
peakgain
                                      -1.680549e+00 at= 1.150000e+00
ngspice 1 -> Q5a.net
Circuit: *title:a5b-aain of nmos inverter
Doing analysis at TEMP = 27.000000 and TNOM = 27.000000
Warning: Pd = 0 is less than W.
Warning: Ps = 0 is less than W.
No. of Data Rows : 301
                                     2.363255e-06
2.472216e+00
voh
                                       2.298608e-01
                                      1.381283e-02
2.597311e-01
      = 2.212485e+00
= 1.381047e-02
                                       -1.884902e+01 at= 2.100000e-01
ngspice 1
```

So, from above considered simulations of load resistance range we can conclude that Threshold(V_M) decreases with increase in load resistance where as Peak gain increases with increase in load resistance.

c)Simulating the circuit

parameters).

Netlist file:

```
File:/home/sivani/A2/Q5c.net

*Title:05c-VTC of NMOS Inverter
.include TSMC180.lib
.model nch_tt nmos

*netlist

Vdd 1 0 2.5
Rl 1 out 75k
Cl out 0 3p
Vin in 0 PULSE(0 2.5 0 0 0 2u 4u)

M1 out in 0 0 nch_tt W=0.54u L=0.18u
.control
tran 0.01u 10u 0u
plot V(out) V(in)
meas tran Voutpeak MAX V(out)
meas tran Voutpeak MAX V(in)
let v1 = Voutpeak/2
let v2 = 0.1*Voutpeak
let v3 = 0.9*Voutpeak
let v4 = Vinpeak/2
meas tran T1 when V(in)=v2 cross=1
meas tran T2 when V(in)=v3 cross=2
meas tran T3 when V(in)=v3 cross=2
meas tran T4 when V(in)=v3 cross=2
meas tran T5 when V(in)=v3 cross=2
meas tran T6 when V(in)=v3 cross=2
meas tran T7 when V(in)=v3 cross=2
meas tran T7 when V(in)=v3 cross=2
meas tran T7 when V(in)=v1 cross=2
meas tran T7 when V(in)=v2 cross=2
meas tran T7 when V(in)=v3 cross=2
meas tran T7 when V(in)=v1 cross=2
meas tran T8 when V(in)=v1 cross=2
meas tran T8 when V(in)=v1 cross=2
meas tran T8 when V(in)=v2 cross=2
meas tran T8 when V(in)=v1 cross=2
meas tran T8 when V(in)=v2 cross=2
meas tran T8 when V(in)=v1 cross=2
meas tran T9 when V(in)=v1
```

```
sivani@sivani-Inspiron-5558: ~/A2
File Edit View Search Terminal Help
out
vin#branch
                                    -2.82365e-11
vdd#branch
No. of Data Rows : 1050
                    = 2.500021e+00 at= 8.000000e-10
voutpeak
                       2.500000e+00 at=
                                           1.000000e-05
                        1.000008e-09
                        9.000076e-09
                        2.019000e-06
                        2.011000e-06
                        5.000044e-09
                        1.282583e-08
                        2.015000e-06
                        2.169378e-06
    8.000068e-09
    8.000000e-09
   l+tph)/2 = -8.11019e-08
```

Here t_r and t_f both are equal to $8x10^{-9}$ approximately. So, both rise and fall time are equal. T_p =8.11 $x10^{-8}$

 We know that maximum operating frequency depends on Tp.Tp is inversely proportional to f(since Ron increases with decrease in W/L).So,Maximum frequency is also inversely proportional to W/L.
 The maximum frequency depends on W,L of mosfet(geometric



Vin-Vout Graph